





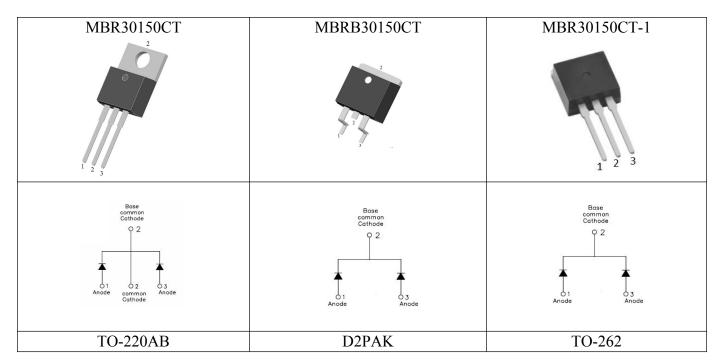
# MBR30150CT/MBRB30150CT-MBR30150CT-1 SCHOTTKY RECTIFIER

#### **Features**

- 150 °C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Applications**

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection



## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	150	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=105°C, rectangular wave form	15(Per Leg) 30(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	200	А

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#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V <sub>F1</sub>	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.81	1.00	V
(Per Leg)*	V <sub>F2</sub>	@ 15A, Pulse, T <sub>J</sub> = 125 °C	0.68	0.8	V
Reverse Current (Per Leg)*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}C$	0.0008	1	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125  ^{\circ}\text{C}$	0.3	6	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	450	760	pF
Typical Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $<sup>^{\</sup>star}\,$  Pulse width < 300  $\mu s,\,$  duty cycle < 2%

#### **Thermal-Mechanical Specifications:**

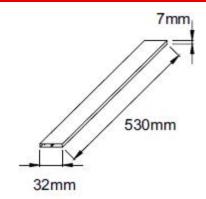
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	DC operation	2.0	°C/W
Typical Thermal Resistance, Case to Heat Sink	$R_{ heta JA}$	DC operation	60	°C/W
Typical Thermal Resistance, Case to Heat Sink	R <sub>θCS</sub>	Mounting surface, smooth and greased	0.50	°C/W
Case Style	TO-220AB D <sup>2</sup> PAK TO-262			

## **Tube Specification**

Device	Package	Weight	Shipping
MBR30150CT	TO-220AB	1.8g	50pcs / tube
MBRB30150CT	D <sup>2</sup> PAK	1.85g	800pcs / reel
MBR30150CT-1	TO-262	1.85g	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Tube Specification(TO-220AB/TO-262)**



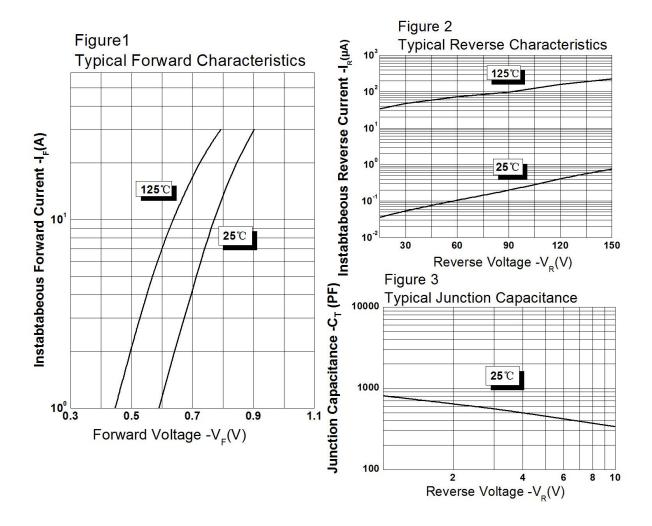
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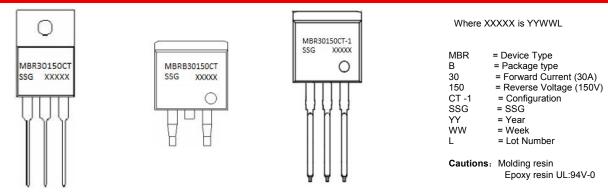




#### **Ratings and Characteristics Curves**



#### **Marking Diagram**



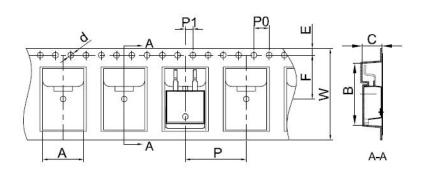
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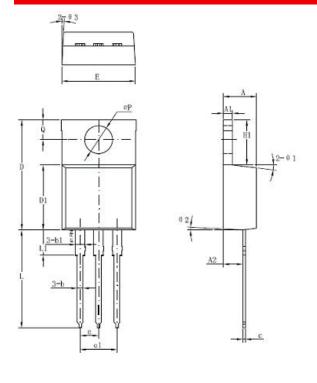


# **Carrier Tape Specification D2PAK**



Symbol	Millimeters		
	Min.	Max.	
А	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

## **Mechanical Dimensions TO-220AB**



Symbol	Millimeters		
	Min.	Typical	Max.
Α	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.52	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
С	0.31	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
е		2.54	
e1	4.98	5.06	5.18
H1	6.04	6.24	6.44
L	12.7	13.56	13.80
L1	3.56	3.5	3.96
ФР	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		7°	
Θ2		3°	
Θ3		4°	

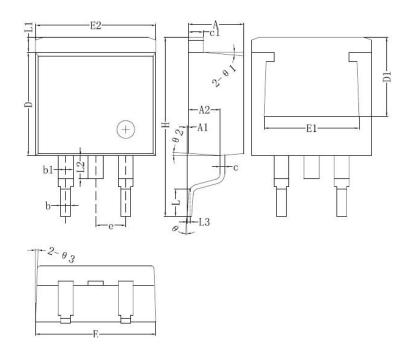
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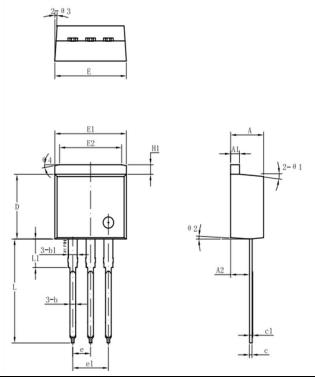


#### **Mechanical Dimensions D<sup>2</sup>PAK**



Symbol	Millimeters			
	Min.	Typical	Max.	
Α	4.47	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.50	8.70	8.90	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.31	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.74	
L1	1.12	1.27	1.42	
L2	1.30		2.20	
L3		0.25BSC		
е	0	-	8°	
e1		5°		
e2		4°		
e3		4°		

## **Mechanical Dimensions TO-262**



Symbol	Millimeters			
	Min.	Typical	Max.	
Α	4.55	4.70	4.85	
<b>A</b> 1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1		1.27		
С	0.36	0.38	0.61	
с1	1.17	1.27	1.37	
D	8.55	8.70	8.85	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.18	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.70	
L1	1.17	1.27	1.40	
L2			2.20	
L3		0.25BSC		
е	0	-	8°	
e1		5°		
e2		4°		
e3		4°		

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#### Technical Data Data Sheet N0767, Rev. B





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